

Claims

1. A solution for removing sidewall residue after dry etching, which comprises sulfuric acid and a fluorine-containing compound, in the range of from 10:1 to 1000:1 by weight.
2. The solution according to claim 1, the range being from 100:1 to 700:1 by weight.
3. The solution according to claim 1, the range being from 300:1 to 500:1 by weight.
4. The solution according to claim 1, the solution containing a fluoride compound, which is composed of fluorine ion and mono-charge cation, the types of this mono-charge cation include alkaline metal cation, ammonium cation and hydrogen ion.
5. The solution according to claim 1, the fluorine-containing compound being hydrogen fluoride.
6. The solution according to claim 1, the fluorine-containing compound being ammonium fluoride.
7. A process for removing sidewall residue after dry etching in which wafer after dry etching is treated with a solution which comprises sulfuric acid and a fluorine-containing compound, in the range of from 10:1 to 1000:1 by weight.
8. The process according to claim 7, the solution being in the range of from 100:1 to 700:1 by weight.

9. The process according to claim 7, the solution being in the range of from 300:1 to 500:1 by weight.

5 10. The process according to claim 7, the fluorine-containing compound is composed of fluorine ion and mono-charge cation, the types of cation include alkaline metal cation, ammonium cation and hydrogen ion.

10 11. The process according to claim 7, the fluorine-containing compound being hydrogen fluoride.

12. The process according to claim 7, the fluorine-containing compound being ammonium fluoride.

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